

N-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	200	
R _{DS(on)} (Ω)	V _{GS} = 10 V	0.91
Q _g (Max.) (nC)	13	
Q _{gs} (nC)	3.0	
Q _{gd} (nC)	7.9	
Configuration	Single	

FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

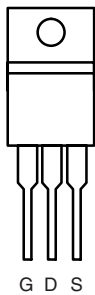


RoHS
COMPLIANT

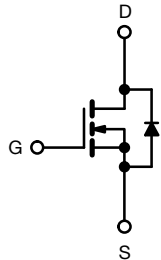
APPLICATIONS

- Primary Side Switch

TO-220AB



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	200	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current	V _{GS} at 10 V	I _D	T _C = 25 °C	A
			T _C = 100 °C	
Pulsed Drain Current ^a		I _{DM}	20	W/°C
Linear Derating Factor			0.33	
Linear Derating Factor (PCB Mount) ^e			0.020	
Single Pulse Avalanche Energy ^b		E _{AS}	161	mJ
Repetitive Avalanche Current ^a		I _{AR}	4.8	A
Repetitive Avalanche Energy ^a		E _{AR}	4.2	mJ
Maximum Power Dissipation	T _C = 25 °C	P _D	42	W
			T _A = 25 °C	
Peak Diode Recovery dV/dt ^c		dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak temperature) ^d		for 10 s	260	



Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- V_{DD} = 50 V, starting T_J = 25 °C, L = 14 mH, R_g = 25 Ω, I_{AS} = 4.8 A (see fig. 12).
- I_{SD} ≤ 5.2 A, di/dt ≤ 95 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Maximum Junction-to-Ambient	R_{thJA}	-	-	110	°C/W	
Maximum Junction-to-Ambient (PCB mount) ^a	R_{thJA}	-	-	50		
Maximum Junction-to-Case (Drain)	R_{thJC}	-	-	3.0		

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	0.29	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 2.9\text{ A}^b$	-	0.91	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 2.9\text{ A}^b$		1.7	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	185	-	μF
Output Capacitance	C_{oss}			-	100	-	
Reverse Transfer Capacitance	C_{rss}			-	30	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 4.8\text{ A}, V_{DS} = 160\text{ V}$, see fig. 6 and 13 ^b	-	-	13.0	nC
Gate-Source Charge	Q_{gs}			-	-	3.0	
Gate-Drain Charge	Q_{gd}			-	-	7.9	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}, I_D = 4.8\text{ A}, R_G = 18\text{ }\Omega, R_D = 20\text{ }\Omega$, see fig. 10 ^b		-	7.2	-	ns
Rise Time	t_r			-	22	-	
Turn-Off Delay Time	$t_{d(off)}$			-	19	-	
Fall Time	t_f			-	13	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	4.8	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	19	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 4.8\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.8	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 4.8\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	150	300	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	0.91	1.8	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

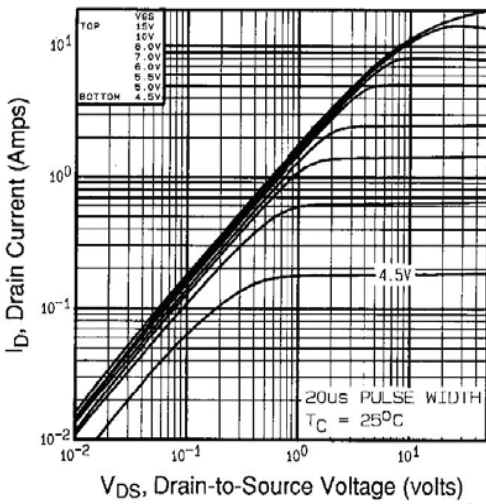


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$



Fig. 3 - Typical Transfer Characteristics



Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$



Fig. 4 - Normalized On-Resistance vs. Temperature



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

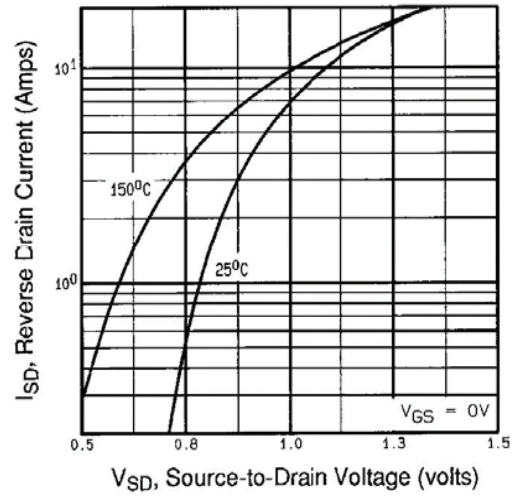


Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 8 - Maximum Safe Operating Area

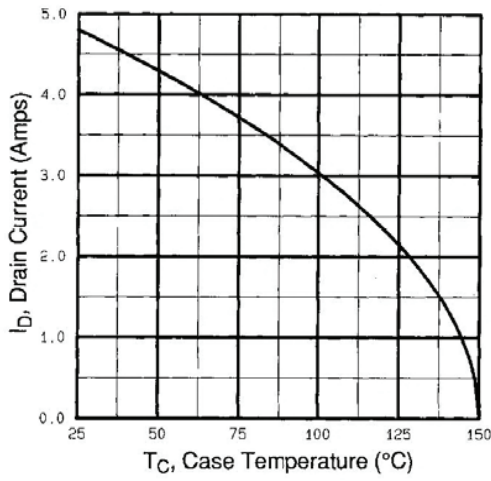


Fig. 9 - Maximum Drain Current vs. Case Temperature

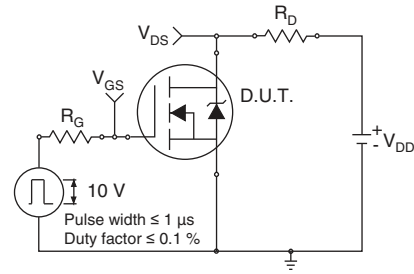


Fig. 10a - Switching Time Test Circuit

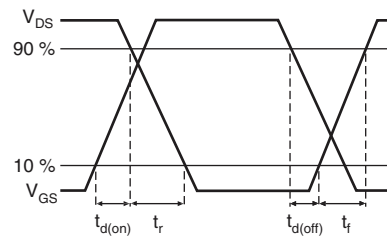


Fig. 10b - Switching Time Waveforms

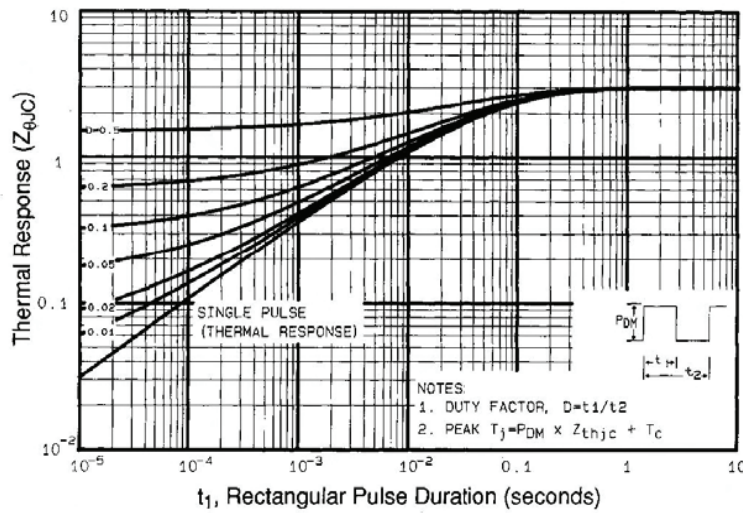


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

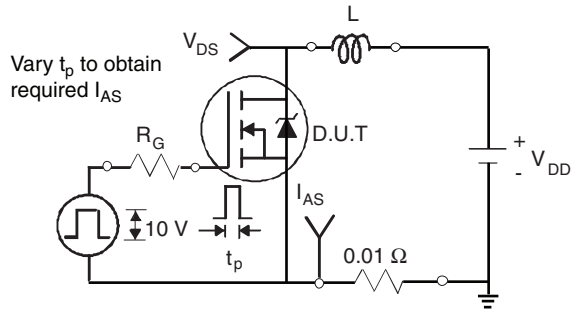


Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms

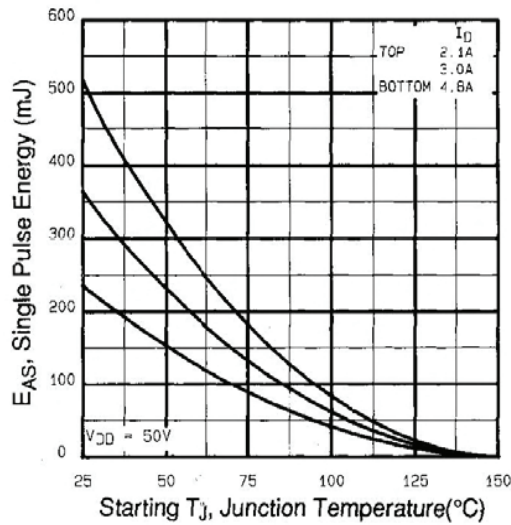


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform

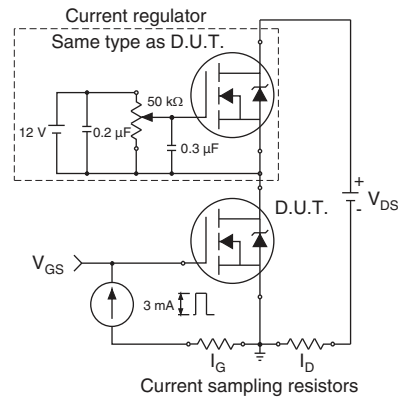
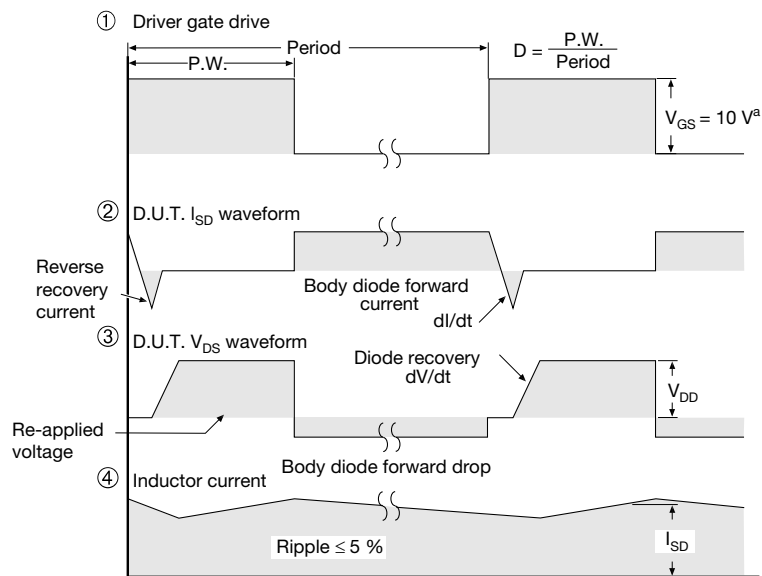
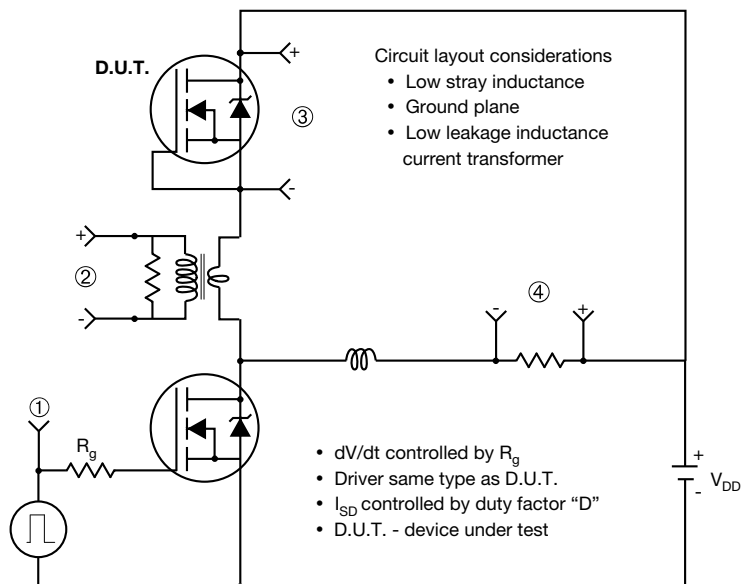


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

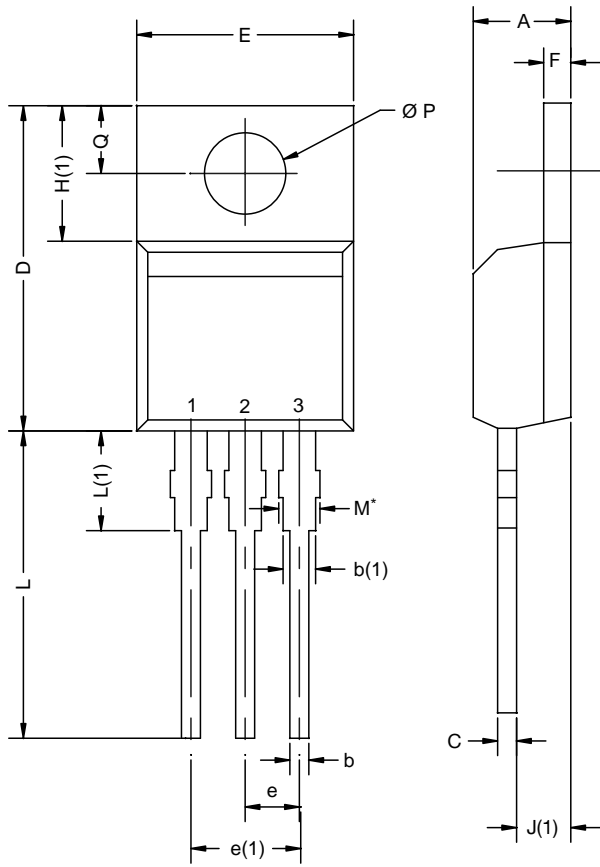


Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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